



Stud diode

Fast Recovery Rectifier Diode

SKN 60F

SKR 60F

Features

- Small recovered charge
- Soft recovery
- Up to 1500 V reverse voltage
- Hermetic metal case with glass insulator
- Threaded studs ISO M6 and M8
- SKN: anode to stud; SKR: cathode to stud

Typical Applications

- Inverse diodes for power transistors, GTO thyristors, asymmetric thyristors
- SMPS, inverters, choppers
- A.C. motor control, uninterruptible power supplies (UPS)

V_{RSM} V	V_{RRM} V	$I_{FRMS} = 120$ A (maximum value for continuous operation) $I_{FAV} = 60$ A (sin. 180; 1000 Hz; $T_c = 100$ °C)		
1200	1200	SKN 60F12	SKR 60F12	
1400	1400	SKN 60F14	SKR 60F14	
1500	1500	SKN 60F15	SKR 60F15	
1700	1700	SKN 60F17	SKR 60F17	

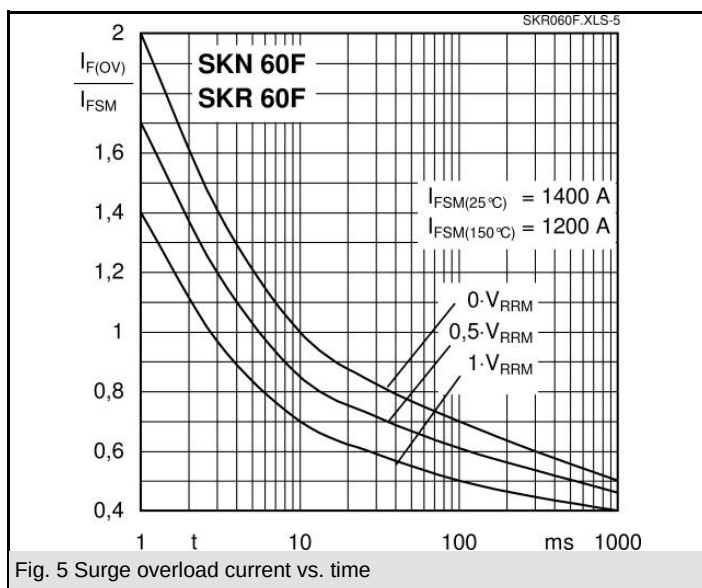
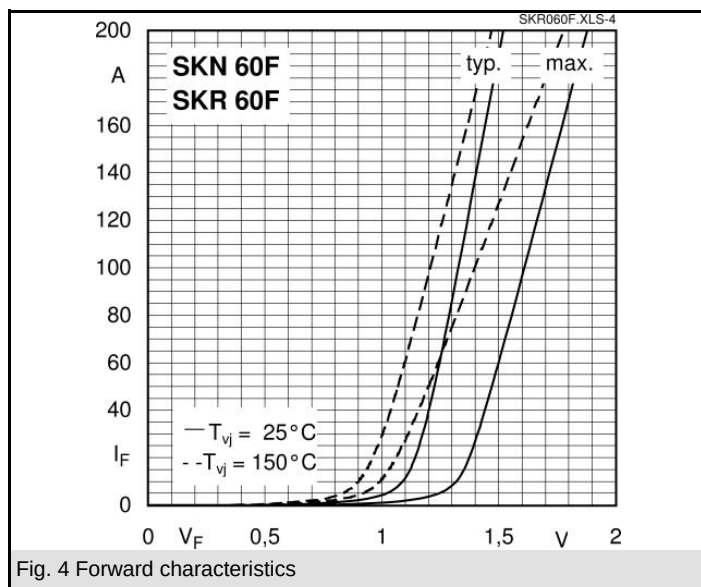
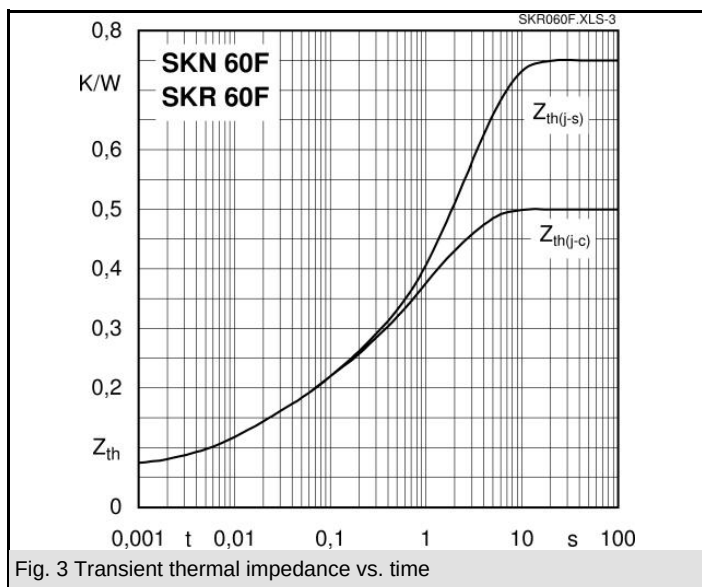
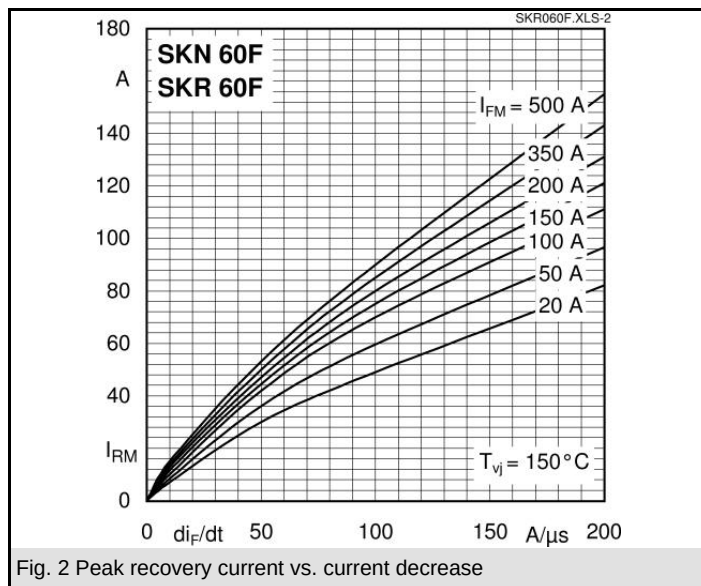
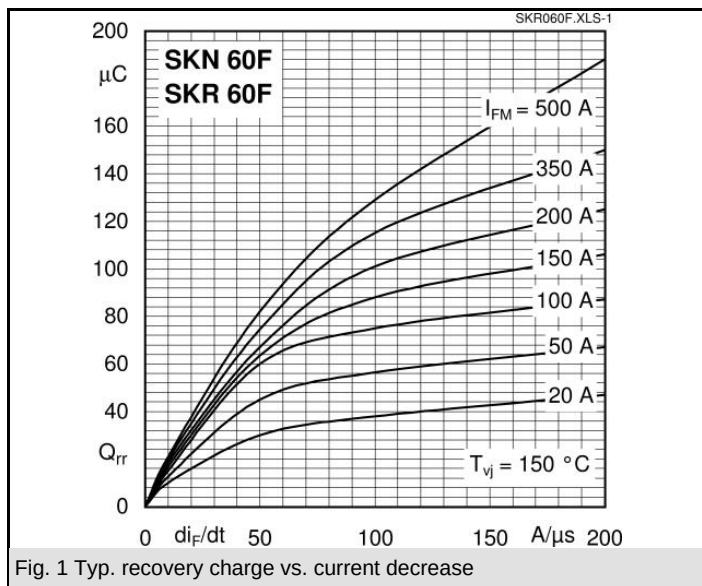
Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 85$ (100) °C	75 (60)	A
I_{FAV}	K3; $T_a = 45$ °C; sin. 180; 1000 Hz	21,5	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms	1400	A
	$T_{vj} = 150$ °C; 10 ms	1200	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	9800	A ² s
	$T_{vj} = 150$ °C; 8,3 ... 10 ms	7200	A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 150$ A	max. 1,75	V
$V_{(TO)}$	$T_{vj} = 150$ °C	max. 1	V
r_T	$T_{vj} = 150$ °C	max. 4	mΩ
I_{RD}	$T_{vj} = 25$ °C; $V_{RD} = V_{RRM}$	max. 0,4	mA
I_{RD}	$T_{vj} = 150$ °C; $V_{RD} = V_{RRM}$	max. 60	mA
Q_{rr}	$T_{vj} = 150$ °C; $I_F = 100$ A,	75	μC
I_{RM}	$-di/dt = 100$ A/μs, $V_R = 30$ V	70	A
t_{rr}		2100	ns
E_{rr}		-	mJ
$R_{th(j-c)}$		0,5	K/W
$R_{th(c-s)}$		0,25	K/W
T_{vj}		- 40 ... + 150	°C
T_{stg}		- 55 ... + 150	°C
V_{isol}		-	V~
M_s	to heatsink	2,5	Nm
a		5 * 9,81	m/s ²
m	approx.	20	g
Case		E 10	

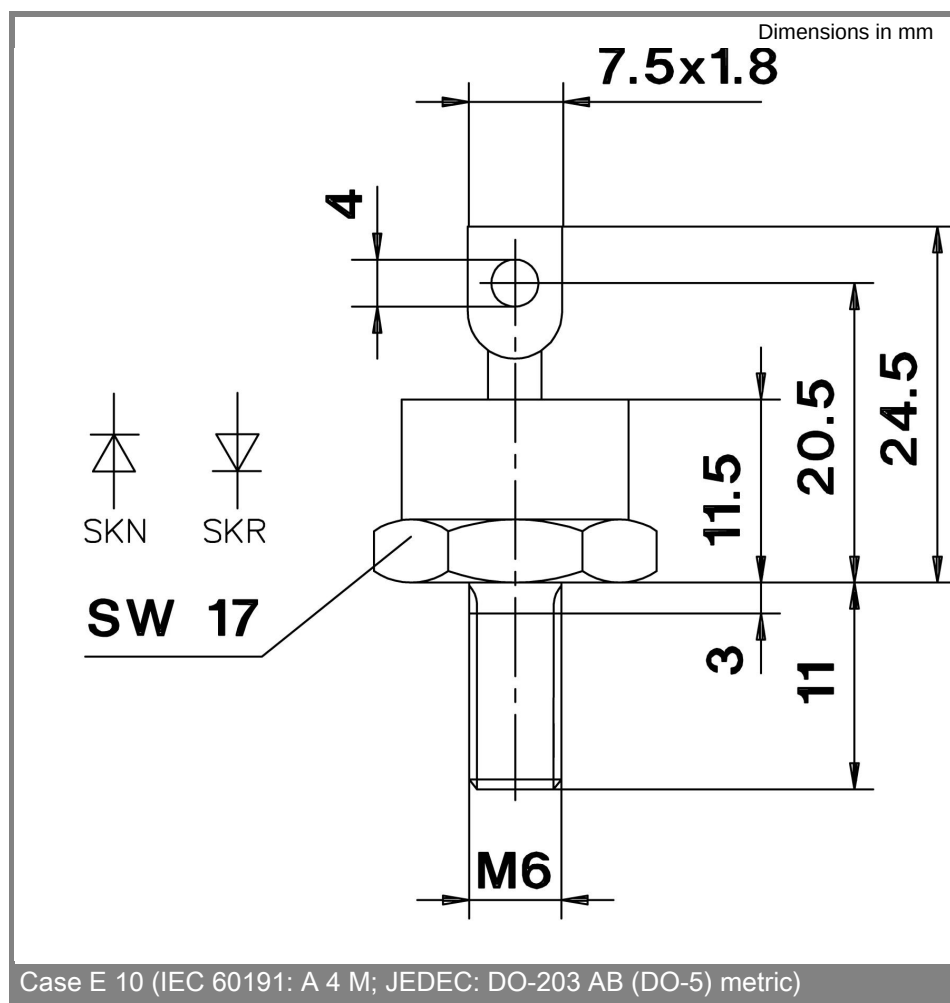


SKN



SKR





This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.